

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (cancelled)

2. (currently amended) A semiconductor device comprising:

a first conducting film formed over ~~on~~ a semiconductor substrate;

a dielectric deposited on said first conducting film;

and

a second conducting film formed on said dielectric,

wherein said dielectric comprises a polycrystalline metal oxide with a first crystallization temperature, having a plurality of crystal grains, and an amorphous metal oxide with a second crystallization temperature higher than the first crystallization temperature, present at boundaries formed between said crystal grains,

wherein a metal material of said polycrystalline metal oxide is different from a metal material of said amorphous metal oxide, and

wherein said polycrystalline metal oxide comprises niobium pentoxide.

3. (currently amended) A semiconductor device comprising:

a first conducting film formed over ~~on~~ a semiconductor substrate;

a dielectric deposited on said first conducting film;
and

a second conducting film formed on said dielectric,

wherein said dielectric comprises a polycrystalline metal oxide with a first dielectric constant and first crystallization temperature, having a plurality of crystal grains, and an amorphous metal oxide, having a lower dielectric constant than said first dielectric constant and a higher crystallization temperature than said first crystallization temperature, present at boundaries formed between said crystal grains,

wherein a metal material of said polycrystalline metal oxide is different from a metal material of said amorphous metal oxide, and

wherein said polycrystalline metal oxide comprises niobium pentoxide.

4. (currently amended) A semiconductor device having a capacitor comprising:

a first electrode of said capacitor comprising a first conducting film formed over ~~on~~ a semiconductor substrate;

a dielectric deposited on said first electrode; and
a second electrode of said capacitor comprising a
second conducting film formed on said dielectric,

wherein the dielectric comprises a polycrystalline
metal oxide with a first crystallization temperature, having
a plurality of crystal grains, and an amorphous metal oxide
with a second crystallization temperature higher than the
first crystallization temperature, present at boundaries
formed between said crystal grains,

wherein a metal material of said polycrystalline metal
oxide is different from a metal material of said amorphous
metal oxide, and

wherein said polycrystalline metal oxide comprises
niobium pentoxide.

Claims 5-9 (cancelled).

10. (original) A semiconductor device according to claim 4,
wherein said first electrode comprises a material selected
from ruthenium, platinum, copper, titanium nitride, tantalum
nitride and tungsten nitride.

11. (currently amended) A semiconductor device according to
claim 4, wherein said first electrode comprises

~~polycrystalline silicon and a silicon oxide film exists between said first electrode and said dielectric.~~

Claims 12-20 (cancelled).

21. (currently amended) A semiconductor device according to claim 2, wherein ~~said polycrystalline oxide comprises niobium pentoxide,~~ and the amorphous metal oxide comprises tantalum pentoxide.

22. (currently amended) A semiconductor device according to claim ~~2~~21, wherein the proportion of the amorphous metal oxide in said dielectric is from 5% to 50%.

23. (currently amended) A semiconductor device according to claim 2, wherein the amorphous metal oxide comprises at least one oxide selected from among tantalum, silicon, titanium, and tungsten.

24. (original) A semiconductor device according to claim 2, wherein the film thickness of said dielectric is from 5 nm to 20 nm.

25. (cancelled).

26. (currently amended) A semiconductor device according to claim 3, wherein said ~~polycrystalline oxide~~ comprises ~~niobium pentoxide,~~ and the amorphous metal oxide comprises tantalum pentoxide.

27. (currently amended) A semiconductor device according to claim ~~3~~26, wherein the proportion of the amorphous metal oxide in said dielectric is from 5% to 50%.

28. (currently amended) A semiconductor device according to claim 3, wherein the amorphous metal oxide comprises at least one oxide selected from among tantalum, silicon, titanium, and tungsten.

29. (original) A semiconductor device according to claim 3, wherein the film thickness of said dielectric is from 5 nm to 20 nm.

30. (cancelled).

31. (currently amended) A semiconductor device according to claim 4, wherein said ~~polycrystalline oxide~~ comprises ~~niobium pentoxide,~~ and the amorphous metal oxide comprises tantalum pentoxide.

32. (currently amended) A semiconductor device according to claim 431, wherein the proportion of the amorphous metal oxide in said dielectric is from 5% to 50%.

33. (currently amended) A semiconductor device according to claim 4, wherein the amorphous metal oxide comprises at least one oxide selected from among tantalum, silicon, titanium, and tungsten.

34. (original) A semiconductor device according to claim 4, wherein the film thickness of said dielectric is from 5 nm to 20 nm.

Claims 35-39 (cancelled).